

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS V -H)

# TPCC8002-H

High-Efficiency DC-DC Converter Applications

Notebook PC Applications

Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge:  $Q_{SW} = 7.1 \text{ nC}$  (typ.)
- Low drain-source ON-resistance:  
 $R_{DS(ON)} = 7.6 \text{ m}\Omega$  (typ.) (  $V_{GS} = 4.5 \text{ V}$  )
- High forward transfer admittance:  $|Y_{fs}| = 65 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 30 \text{ V}$ )
- Enhancement mode:  $V_{th} = 1.5 \text{ to } 2.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

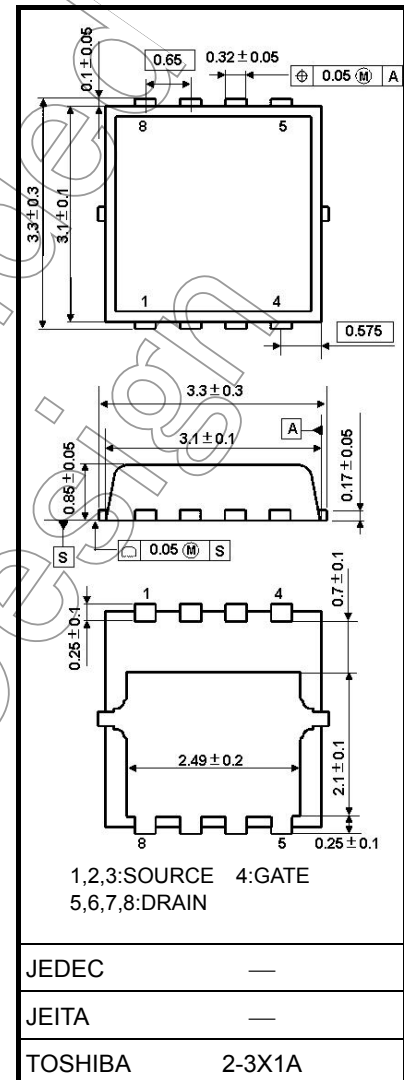
| Characteristic  |                 | Symbol    | Rating     | Unit             |
|---|-----------------|-----------|------------|------------------|
| Drain-source voltage  |                 | $V_{DSS}$ | 30         | V                |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )              |                 | $V_{DGR}$ | 30         | V                |
| Gate-source voltage   |                 | $V_{GSS}$ | $\pm 20$   | V                |
| Drain current   | DC (Note 1)     | $I_D$     | 22         | A                |
|   | Pulsed (Note 1) | $I_{DP}$  | 66         | A                |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ )              |                 | $P_D$     | 30         | W                |
| Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)          |                 | $P_D$     | 1.9        | W                |
| Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)          |                 | $P_D$     | 0.7        | W                |
| Single-pulse avalanche energy (Note 3)                            |                 | $E_{AS}$  | 126        | mJ               |
| Avalanche current   |                 | $I_{AR}$  | 22         | A                |
| Repetitive avalanche energy ( $T_c = 25^\circ\text{C}$ ) (Note 4) |                 | $E_{AR}$  | 2.1        | mJ               |
| Channel temperature   |                 | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature range   |                 | $T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

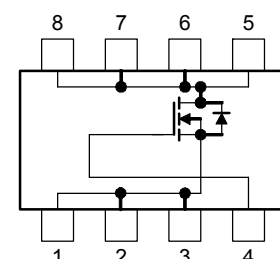
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.02 g (typ.)

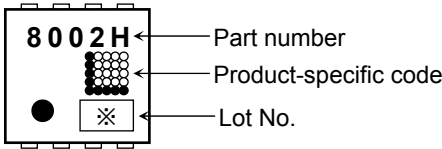
## Circuit Configuration



Thermal Characteristics

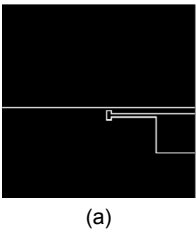
| Characteristic  | Symbol          | Max | Unit                 |
|---|-----------------|-----|----------------------|
| Thermal resistance, channel to case<br>( $T_c = 25^{\circ}\text{C}$ )     | $R_{th (ch-c)}$ | 4.2 | $^{\circ}\text{C/W}$ |
| Thermal resistance, channel to ambient<br>( $t = 10\text{ s}$ ) (Note 2a) | $R_{th (ch-a)}$ | 66  | $^{\circ}\text{C/W}$ |
| Thermal resistance, channel to ambient<br>( $t = 10\text{ s}$ ) (Note 2b) | $R_{th (ch-a)}$ | 180 | $^{\circ}\text{C/W}$ |

Marking (Note 5)

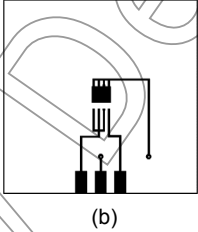


Note 1: Ensure that the channel temperature does not exceed  $150^{\circ}\text{C}$ .

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4  
 $25.4 \times 25.4 \times 0.8$   
(Unit: mm)

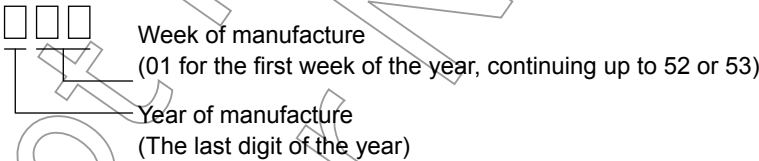


FR-4  
 $25.4 \times 25.4 \times 0.8$   
(Unit: mm)

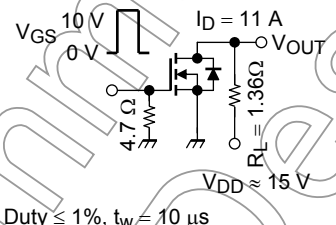
Note 3:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial),  $L = 200\text{ }\mu\text{H}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AR} = 22\text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

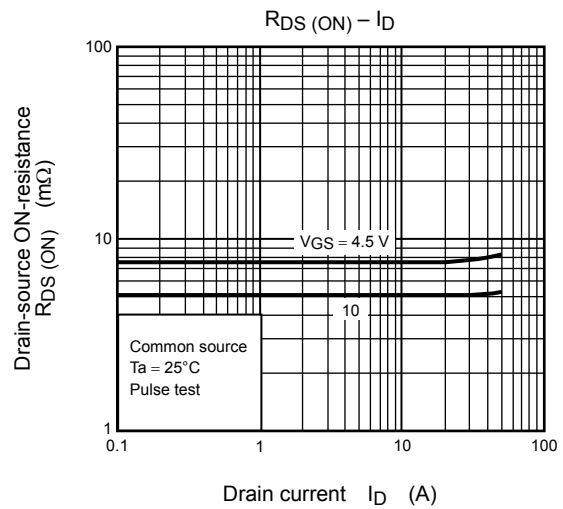
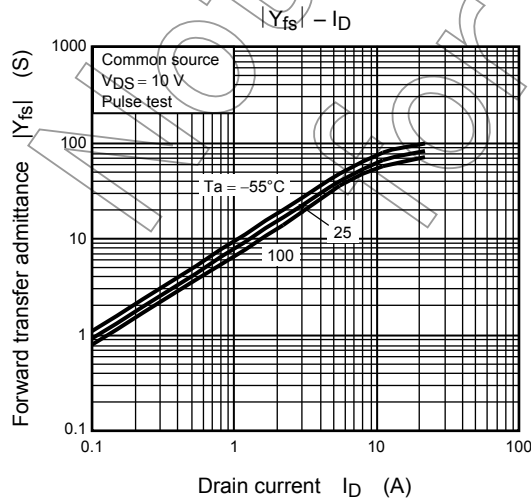
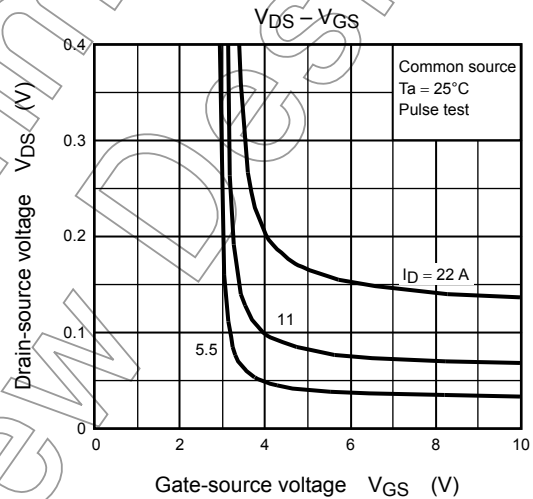
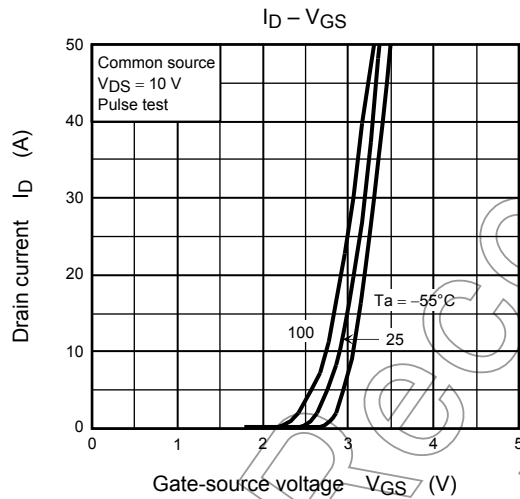
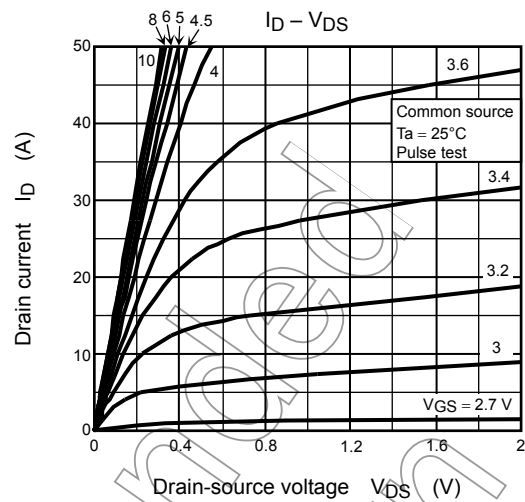
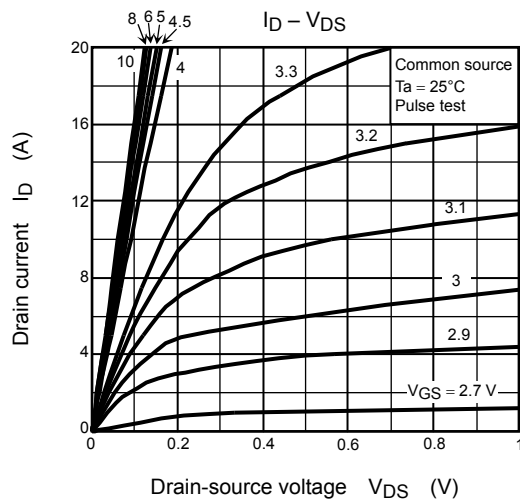


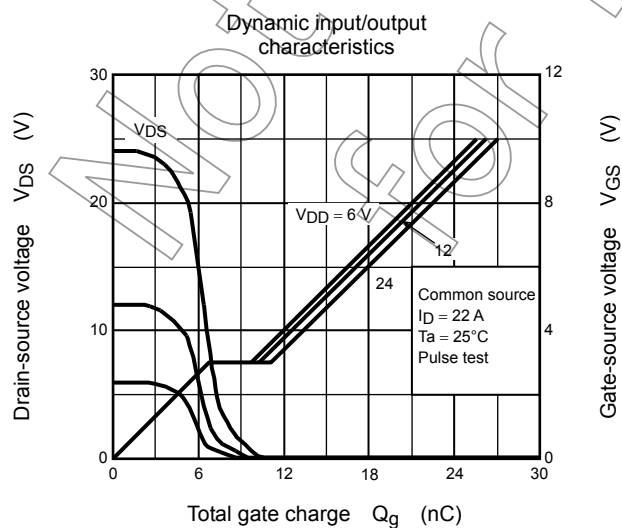
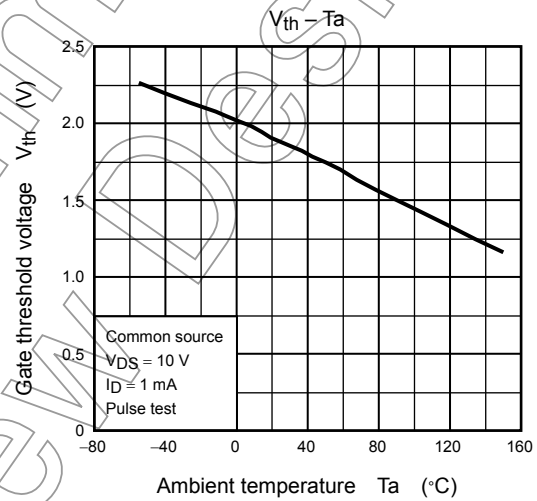
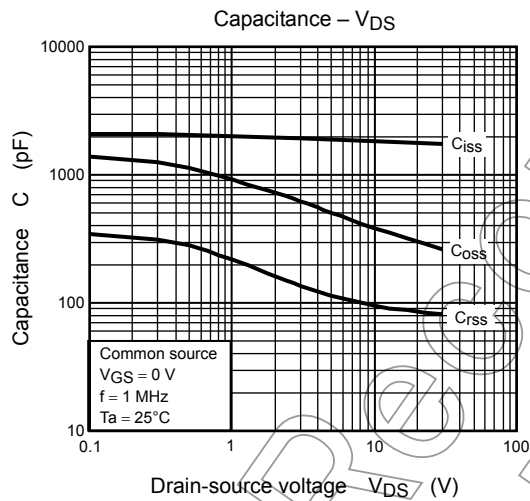
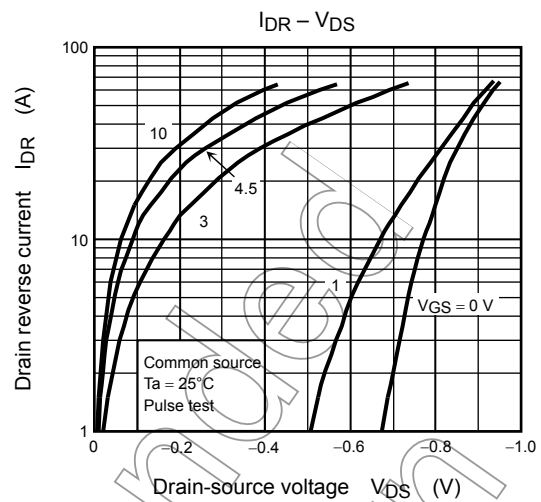
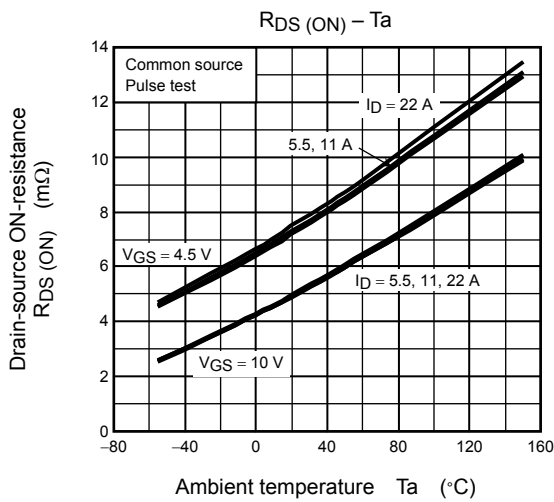
## Electrical Characteristics (Ta = 25°C)

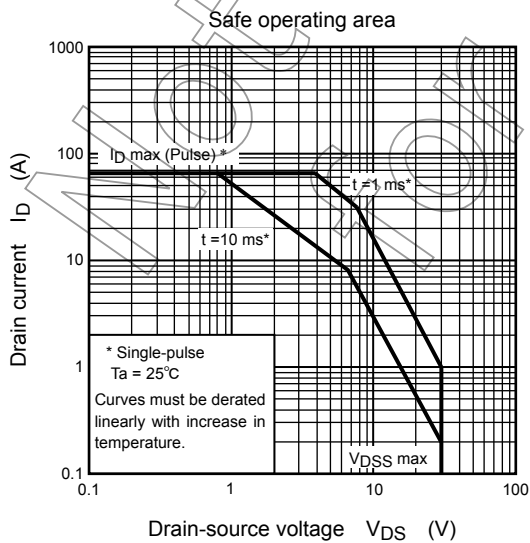
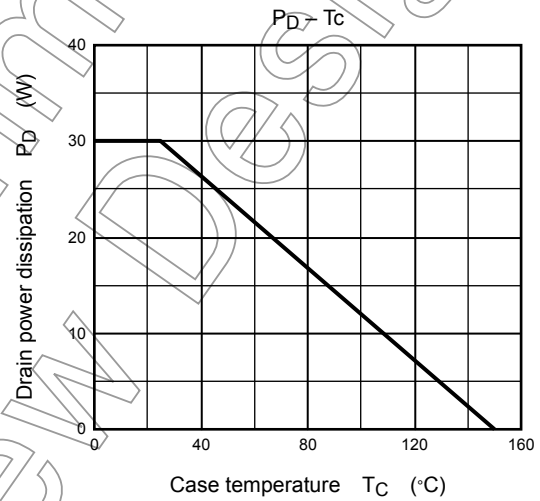
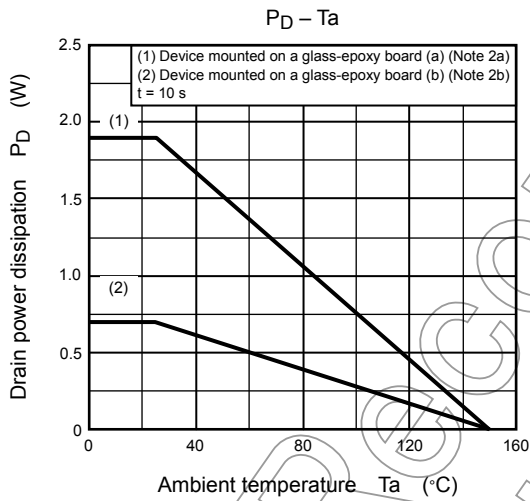
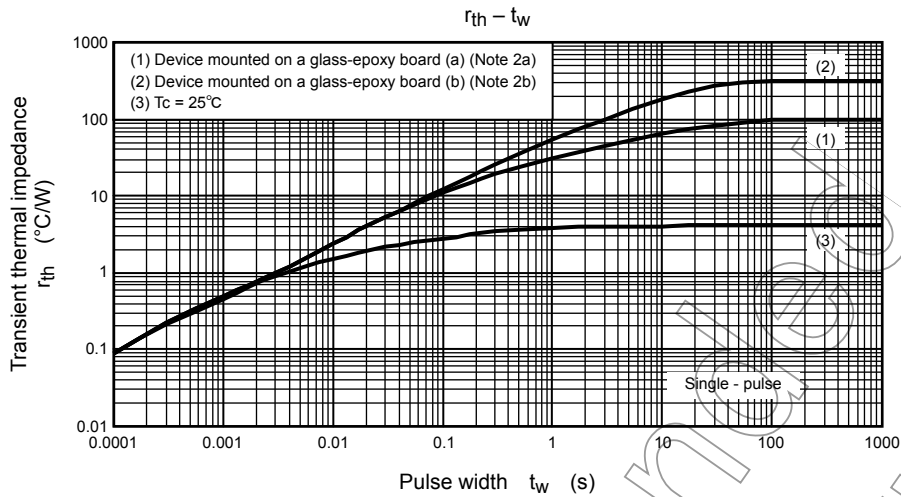
| Characteristic                                  |               | Symbol               | Test Condition  | Min                               | Typ. | Max  | Unit |
|---|---------------|----------------------|---|-----------------------------------|------|------|------|
| Gate leakage current                            |               | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V                                      | —                                 | —    | ±100 | nA   |
| Drain cutoff current                            |               | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                                       | —                                 | —    | 10   | μA   |
| Drain-source breakdown voltage                  |               | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                                       | 30                                | —    | —    | V    |
|   |               | V (BR) DSX           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V                                     | 15                                | —    | —    |      |
| Gate threshold voltage                          |               | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                                       | 1.5                               | —    | 2.5  | V    |
| Drain-source ON-resistance                      |               | R <sub>DS (ON)</sub> | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 11 A                                      | —                                 | 7.6  | 10.6 | mΩ   |
|   |               |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A                                       | —                                 | 5.5  | 8.3  |      |
| Forward transfer admittance                     |               | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A                                       | 33                                | 65   | —    | S    |
| Input capacitance                               |               | C <sub>iss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                            | —                                 | 1900 | 2500 | pF   |
| Reverse transfer capacitance                    |               | C <sub>rss</sub>     |   | —                                 | 110  | 170  |      |
| Output capacitance                              |               | C <sub>oss</sub>     |   | —                                 | 400  | —    |      |
| Gate resistance                                 |               | r <sub>g</sub>       | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz                            | —                                 | 3.2  | 4.8  | Ω    |
| Switching time                                  | Rise time     | t <sub>r</sub>       |  | —                                 | 2.8  | —    | ns   |
|   | Turn-on time  | t <sub>on</sub>      |   | —                                 | 9.8  | —    |      |
|   | Fall time     | t <sub>f</sub>       |   | —                                 | 5.9  | —    |      |
|   | Turn-off time | t <sub>off</sub>     |   | Duty ≤ 1%, t <sub>w</sub> = 10 μs | —    | 27   |      |
| Total gate charge (gate-source plus gate-drain) |               | Q <sub>g</sub>       | V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22 A               | —                                 | 27   | —    | nC   |
|   |               |                      | V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 22 A                | —                                 | 14.3 | —    |      |
| Gate-source charge 1                            |               | Q <sub>gs1</sub>     | V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22 A               | —                                 | 6.8  | —    |      |
| Gate-drain ("Miller") charge                    |               | Q <sub>gd</sub>      |   | —                                 | 4.3  | —    |      |
| Gate switch charge                              |               | Q <sub>SW</sub>      |   | —                                 | 7.1  | —    |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic          |                | Symbol    | Test Condition                                | Min | Typ. | Max  | Unit |
|-------------------------|----------------|-----------|---|-----|------|------|------|
| Drain reverse current   | Pulse (Note 1) | $I_{DRP}$ | —   | —   | —    | 66   | A    |
| Forward voltage (diode) |                | $V_{DSF}$ | $I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$ | —   | —    | -1.2 | V    |







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